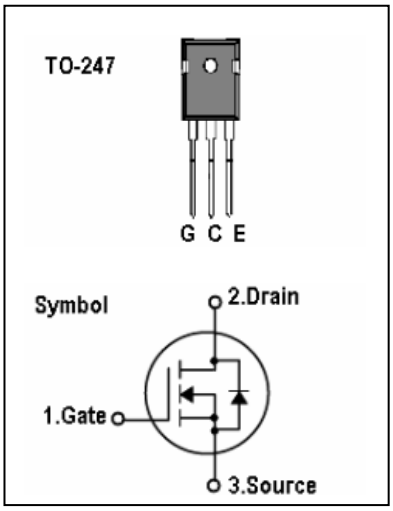
N-Channel MOSFET



Features

- 80V,350A,Rds(on)(typ)=2.0mΩ @Vgs=10V
- High Ruggedness
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability

General Description

This Power MOSFET is produced using DeXin's advanced Trench MOS Technology. This latest technology has been especially designed to minimize on-state resistance, have a high rugged avalanche characteristics. These devices are well suited for low voltage application such as automotive,DC/DC converters,and high efficiency switch for power management in portable and battery products.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	80	V
I_D	Continuous Drain Current (T_C=25 ℃)	350	A
	Continuous Drain Current (T_C=100℃)	240	A
I_{DM}	Pulsed Drain Current (Note 1)	1400	A
V_{GS}	Gate-Source Voltage	±25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	2000	mJ
P_D	Maximum Power Dissipation (T_C=25 ℃)	500	W
	Derating Factor above 25℃	2.0	W/℃
T_J	Operating Junction Temperature Range	-55 to +175	℃
T_{STG}	Storage Temperature Range	-55 to +175	℃

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case	0.4	℃/ W
$R_{th\ c\text{-}s}$	Thermal Resistance, Case to Sink	0.4	℃/ W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	62.5	℃/ W

Electrical Characteristics (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	80	-	-	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V, V_{GS}=0V	-	-	250	uA
I_{GSS}	Gate Leakage Current, Forward	V_{GS}=25V, V_{DS}=0V	-	-	100	nA
	Gate Leakage Current, Reverse	V_{GS}=-25V, V_{DS}=0V	-	-	-100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS}, I_D=250uA	2	-	4	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=80A	-	2.0	2.5	mΩ
Qg	Total Gate Charge	V_{DD}=60V	-	420	-	nC
Qgs	Gate-Source Charge	V_{GS}=10V	-	110	-	nC
Qgd	Gate-Drain Charge	I_D=175A (Note 3)	-	180	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=60V,V_{GS}=10V	-	35	-	ns
t_r	Turn-on Rise Time	I_D=175A,R_G=1Ω	-	47	-	ns
$t_{d(off)}$	Turn-off Delay Time	T_C=25 ℃	-	42	-	ns
t_f	Turn-off Fall Time	(Note 3)	-	36	-	ns
Ciss	Input Capacitance -	V_{DS}=25V	-	20000	-	pF
Coss	Output Capacitance	V_{GS}=0V	-	2100	-	pF
Crss	Reverse Transfer Capacitance	f = 1MHz	-	950	-	pF

Source-Drain Diode Characteristics (T_C=25℃ unless otherwise noted)

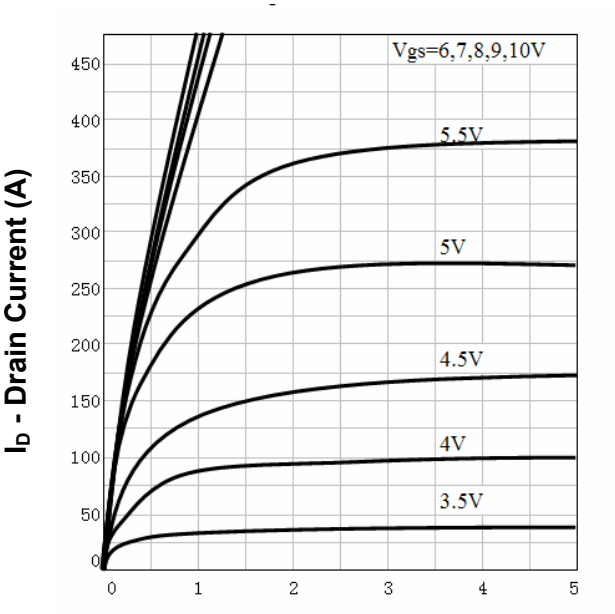
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Diode Forward Current		-	-	350	A
I_{SM}	Pulsed Source Diode Forward Current (Note 1)		-	-	1400	A
V_{SD}	Forward On Voltage	V_{GS}=0V, I_S=175A	-	-	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V, I_S=175A	-	125	168	ns
Q_{rr}	Reverse Recovery Charge	dI_F/dt = 100A/us	-	460	730	nC

Notes：

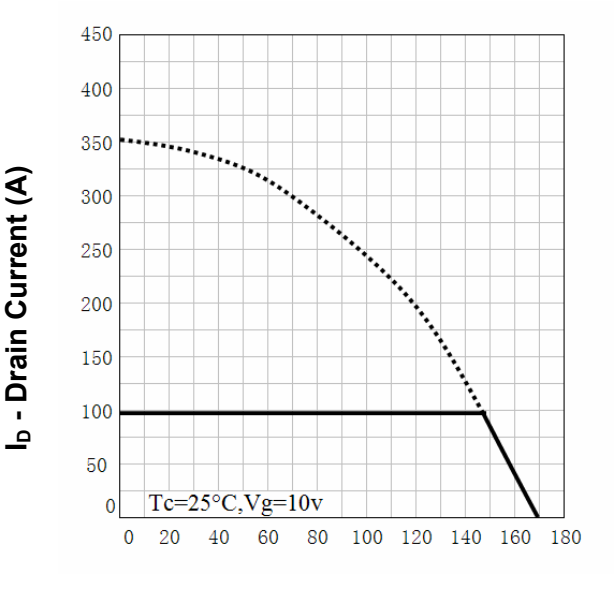
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=0.28mH, I_{AS}=100A, V_{DD}=45V, R_G=25Ω , Starting T_J=25℃
3. Pulse Width ≤ 300 us; Duty Cycle≤2%

Typical Characteristics

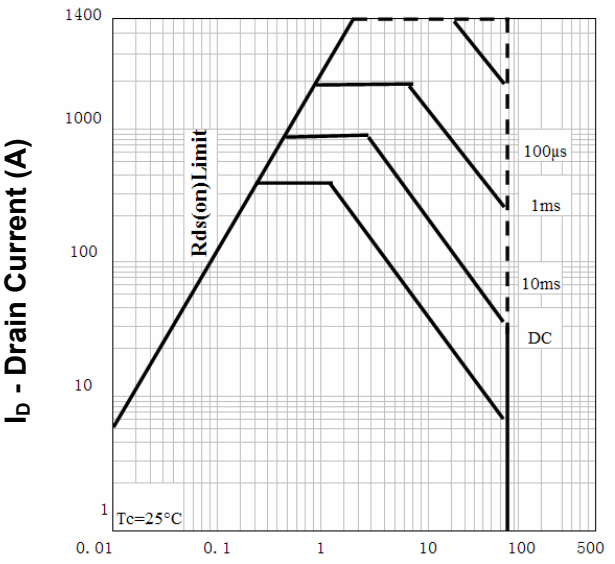
Output Characteristics



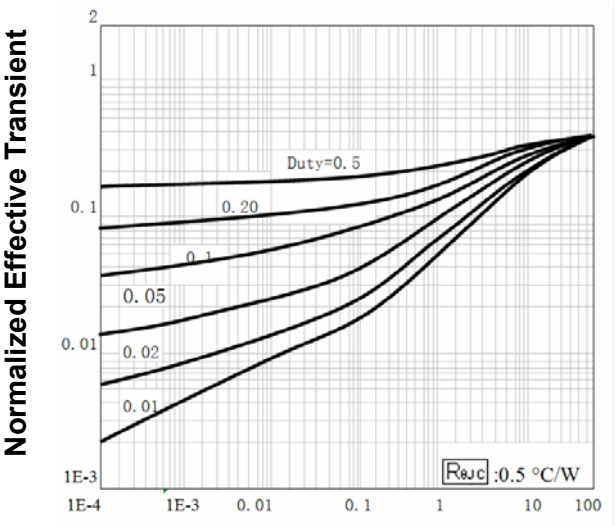
Drain Current



Safe Operation Area

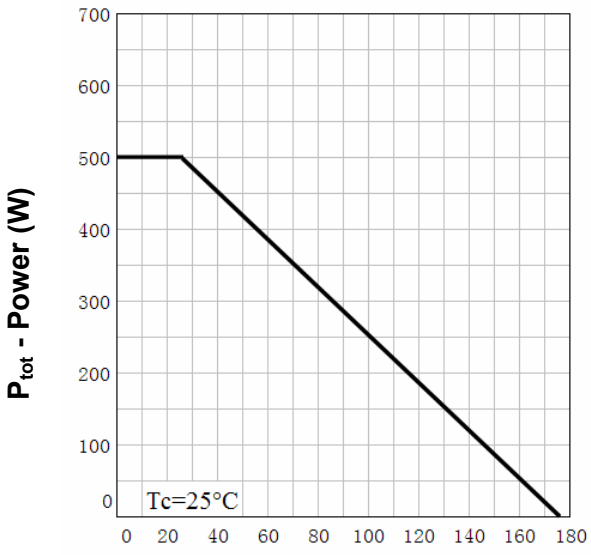


Thermal Transient Impedance

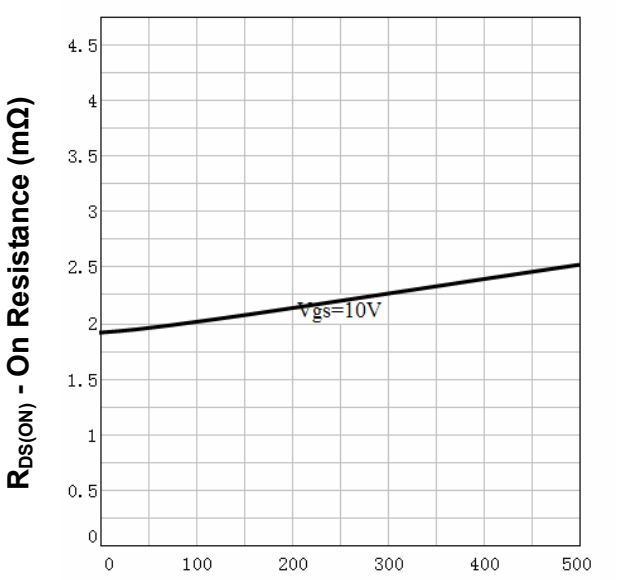


Typical Characteristics

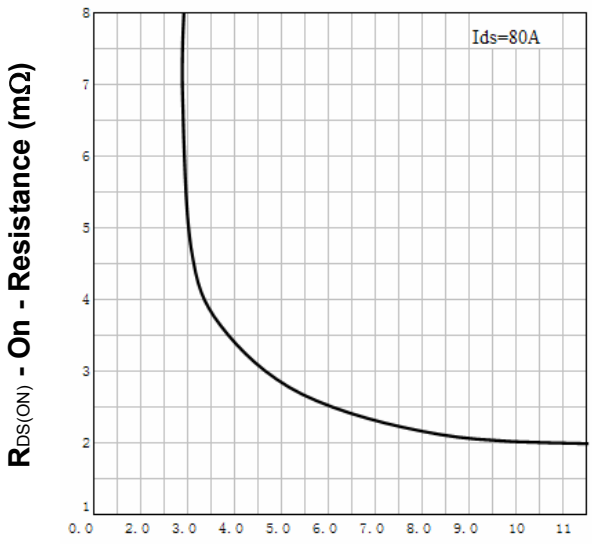
Power Dissipation



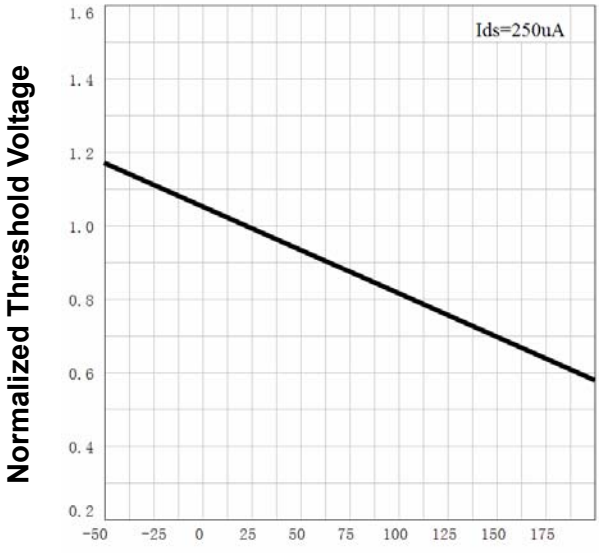
Drain-Source On Resistance



Drain-Source On Resistance

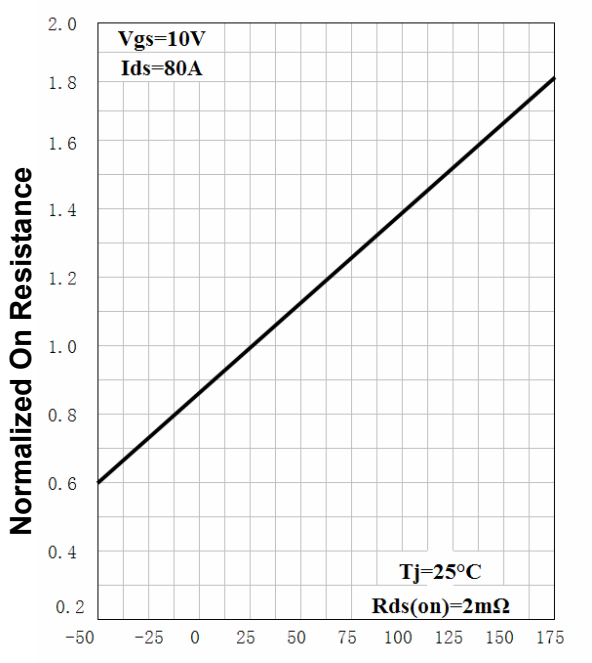


Gate Threshold Voltage



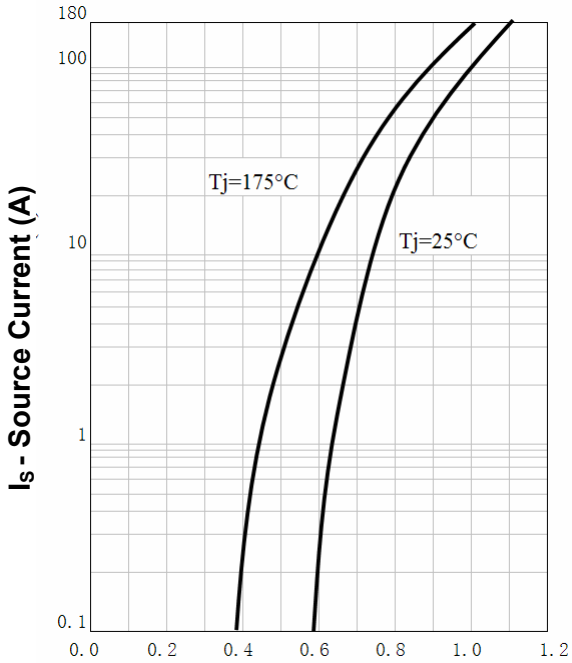
Typical Characteristics

Drain-Source On Resistance



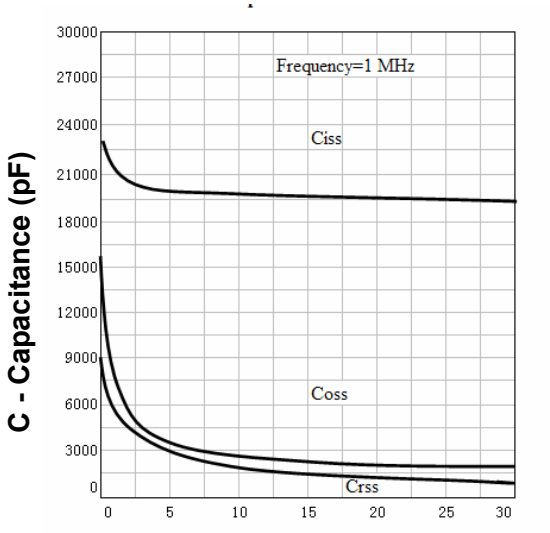
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



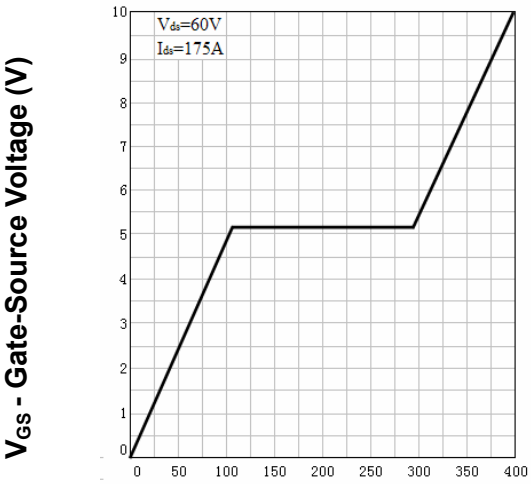
V_{SD} - Source-Drain Voltage (V)

Capacitance



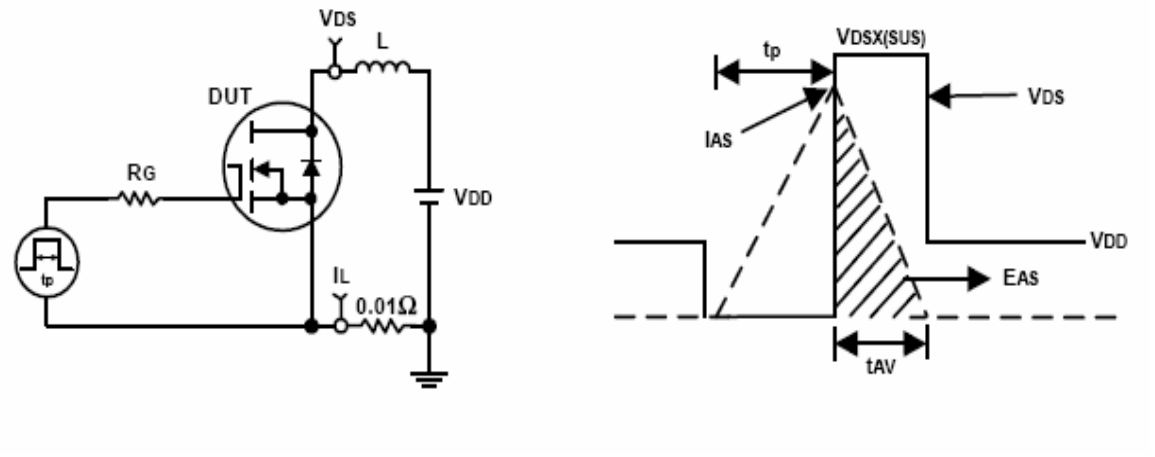
V_{DS} - Drain-Source Voltage (V)

Gate Charge



Q_G - Gate Charge (nC)

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms